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Substitute for form 1449A/PTO

INFORMATION DISCLOSURE STATEMENT BY APPLICANT

(use as many sheets as necessary)

Sheet 1 of 3

	Complete if Known
Application Number	10/791,633
Filing Date	03/01/2004
First Named Inventor	Maalouf, Khalil J.
Art Unit	Not yet known
Examiner Name	Not yet known
Attorney Docket Number	019930-002510US

			U.S. PATENT DO	DCUMENTS+	
Examiner Initials*	Cite No.'	Document Number Number Kind Code ² (if known)	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures.Appear
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		Country Code ³	Number ⁴	Kind Code ^s (if known)	Publication Date MM-DD-YYYY	Applicant of Cited Document	Where Relevant Passages or Relevant Figures Appear	т⁰
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Substitute for form 1449B/PTO Complete if Known Application Number 10/791,633 **INFORMATION DISCLOSURE** 03/01/2004 Filing Date STATEMENT BY APPLICANT Maalouf, Khalil J. First Named Inventor Art Unit Not yet known (use as many sheets as necessary) Examiner Name Not yet known Sheet 2 3 Attorney Docket Number 019930-002510US

		NON PATENT LITERATURE DOCUMENTS	
Examiner Initials *	Cite No.1	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.	T²
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MICO	DALATI	0N 010	OL OCUBE	Application Number	10/791,633	
			CLOSURE	Filing Date	03/01/2004	
STAT	EMEN	I BY A	PPLICANT	First Named Inventor	Maalouf, Khalil J.	
				Art Unit	Not yet known	
((use as many sheets as necessary)		Examiner Name	Not yet known		
Sheet	3	of	3	Attorney Docket Number	019930-002510US	

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